

N-Ch 20V Fast Switching MOSFETs

Features:

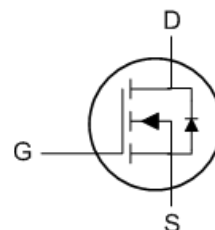
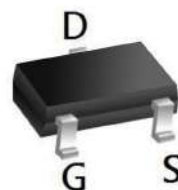
- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent Cdv/dt effect decline
- ★ Advanced high cell density Trench technology

Description:

The KWUC2510 is the high cell density trench N-ch MOSFETs, which provides excellent RDS(on) and efficiency for most of the small power switching and load switch applications.

The KWUC2510 meet the RoHS and Green Product requirement with full function reliability approved.

SOT23S Pin Configuration



Product Summary

BVDSS	RDS(on)	ID
20V	26mΩ	6.0A

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	20	V
V_{GS}	Gate-Source Voltage	± 12	V
$I_D@T_A=25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 4.5V^1$	6.0	A
$I_D@T_A=70^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 4.5V^1$	5.0	A
I_{DM}	Pulsed Drain Current ²	17	A
$P_D@T_A=25^\circ\text{C}$	Total Power Dissipation ³	1	W
$P_D@T_A=70^\circ\text{C}$	Total Power Dissipation ³	0.66	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient ¹	120	$^\circ\text{C/W}$

Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	20	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BVDSS Temperature Coefficient	Reference to 25°C , $I_D=1mA$	---	0.018	---	$V/^\circ\text{C}$
$R_{DS(on)}$	Static Drain-Source On-Resistance ²	$V_{GS}=4.5V, I_D=4A$	---	21	26	$m\Omega$
		$V_{GS}=2.5V, I_D=3A$	---	28	35	
		$V_{GS}=1.8V, I_D=2A$	---	40	50	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\mu A$	0.45	---	1.0	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-3.1	---	$mV/^\circ\text{C}$
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=16V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	1	μA
		$V_{DS}=16V, V_{GS}=0V, T_J=55^\circ\text{C}$	---	---	5	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 12V, V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=5V, I_D=4A$	---	30	---	S
Q_g	Total Gate Charge (4.5V)	$V_{DS}=15V, V_{GS}=4.5V, I_D=4A$	---	8.6	---	nC
Q_{gs}	Gate-Source Charge		---	1.37	---	
Q_{gd}	Gate-Drain Charge		---	2.3	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DS}=10V, V_{GS}=4.5V, R_G=3.3\Omega, I_D=4A$	---	5.2	---	ns
T_r	Rise Time		---	34	---	
$T_{d(off)}$	Turn-Off Delay Time		---	23	---	
T_f	Fall Time		---	9.2	---	
C_{iss}	Input Capacitance	$V_{DS}=15V, V_{GS}=0V, f=1MHz$	---	670	---	pF
C_{oss}	Output Capacitance		---	75	---	
C_{rss}	Reverse Transfer Capacitance		---	68	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,4}	$V_G=V_D=0V$, Force Current	---	---	6	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V, I_S=1A, T_J=25^\circ\text{C}$	---	---	1.2	V

Note :

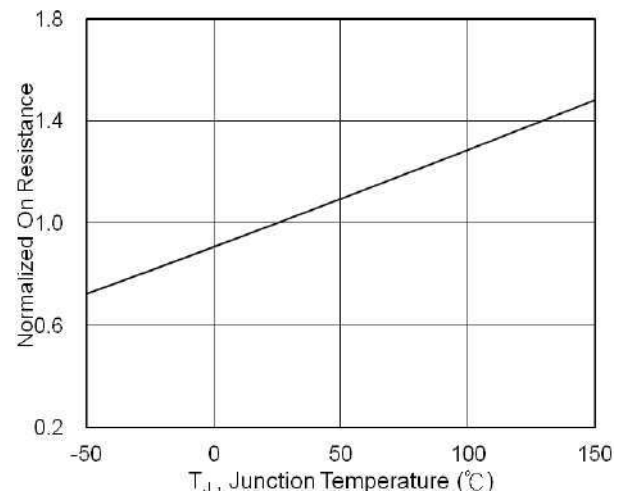
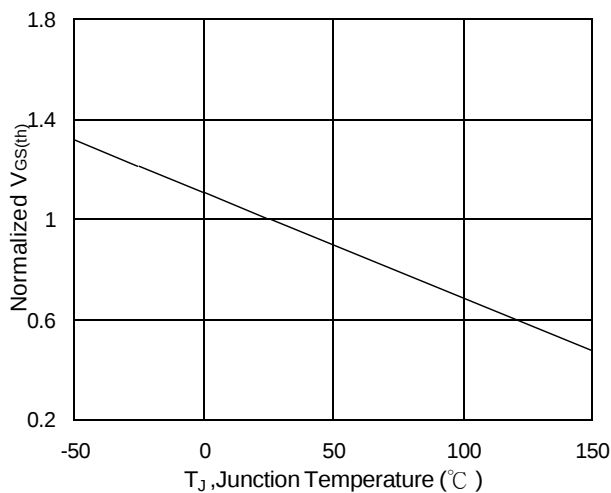
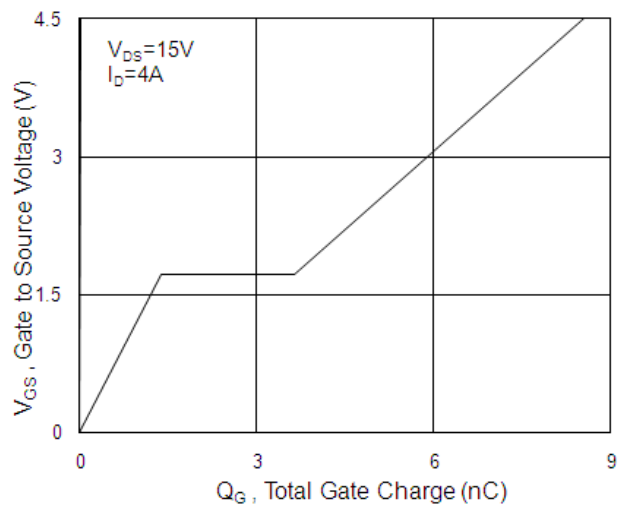
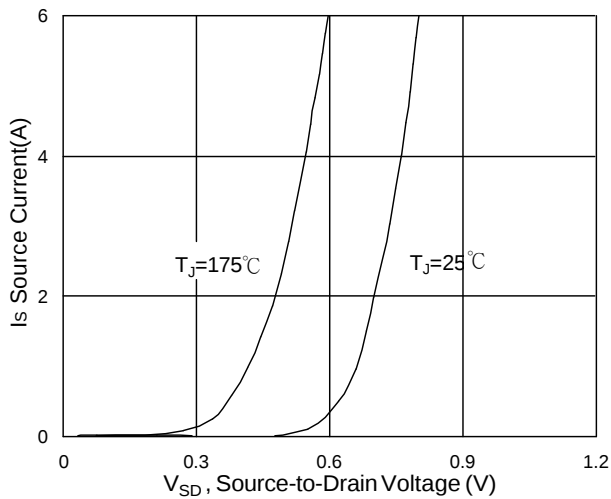
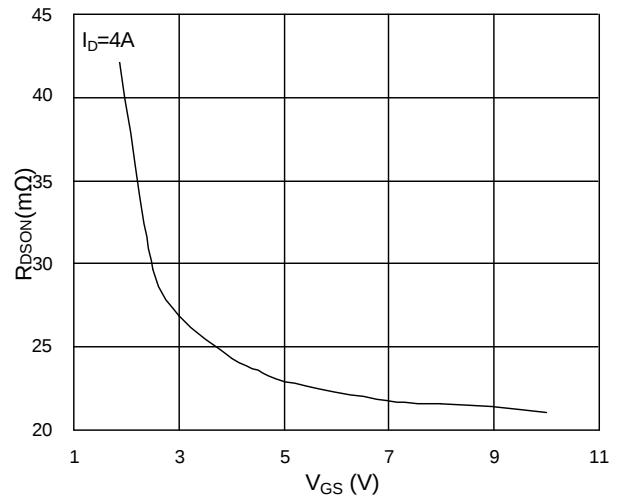
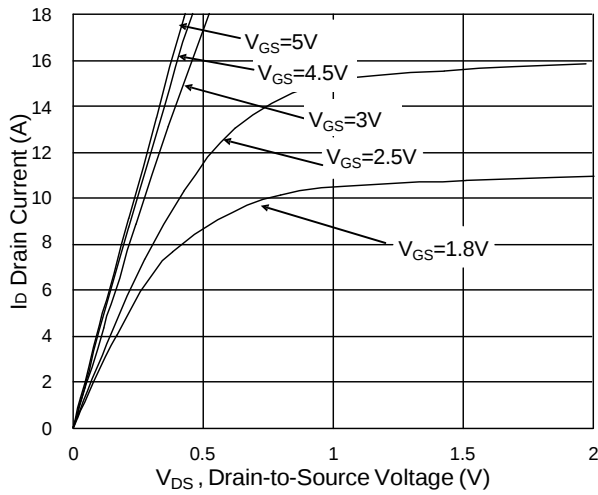
1. The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper.

2. The data tested by pulsed, pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$

3. The power dissipation is limited by 150°C junction temperature

4. The data is theoretically the same as I_D and I_{DM} , in real applications, should be limited by total power dissipation.

Typical Characteristics



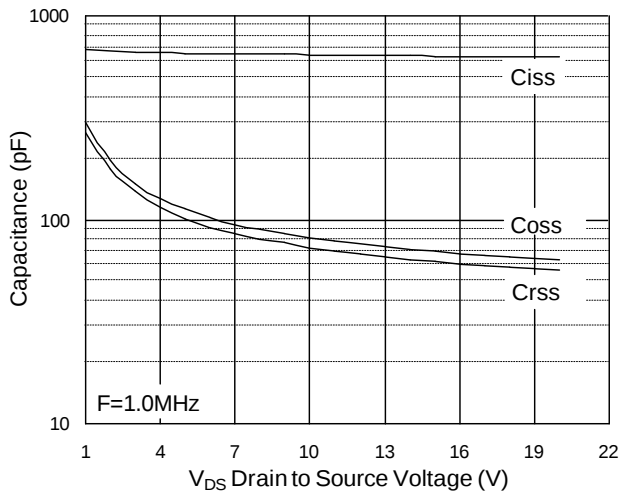


Fig.7 Capacitance

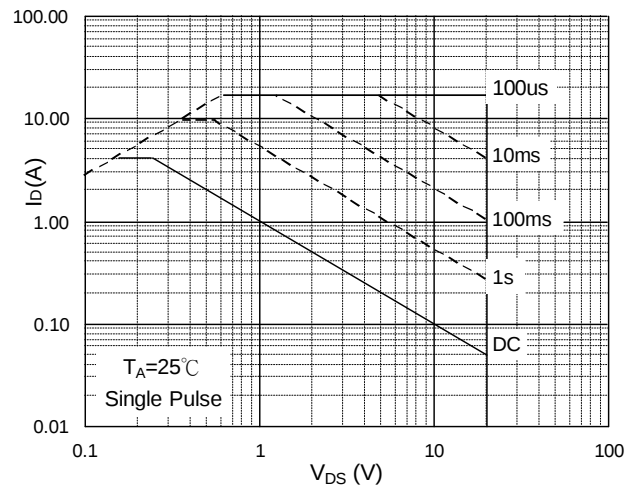


Fig.8 Safe Operating Area

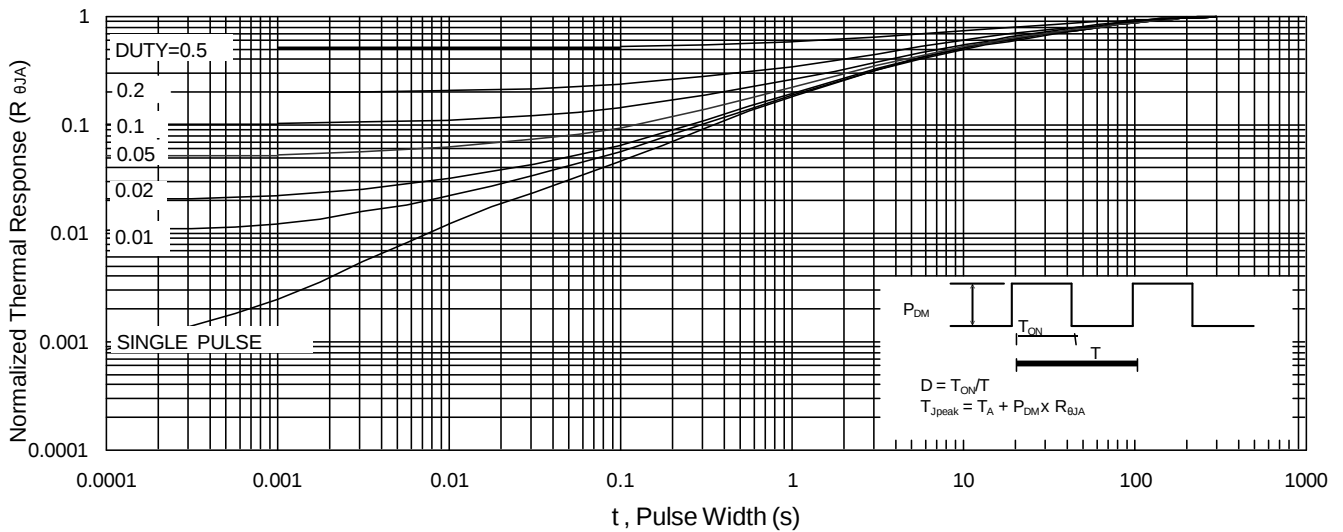


Fig.9 Normalized Maximum Transient Thermal Impedance

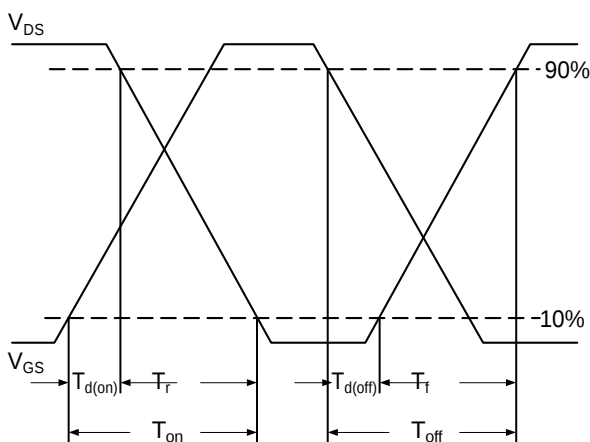


Fig.10 Switching Time Waveform

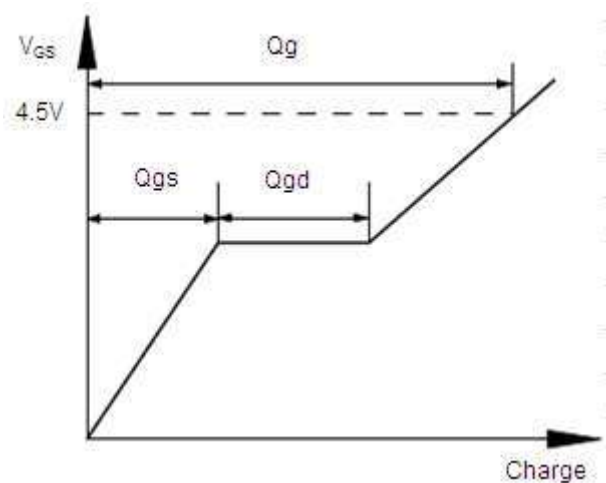
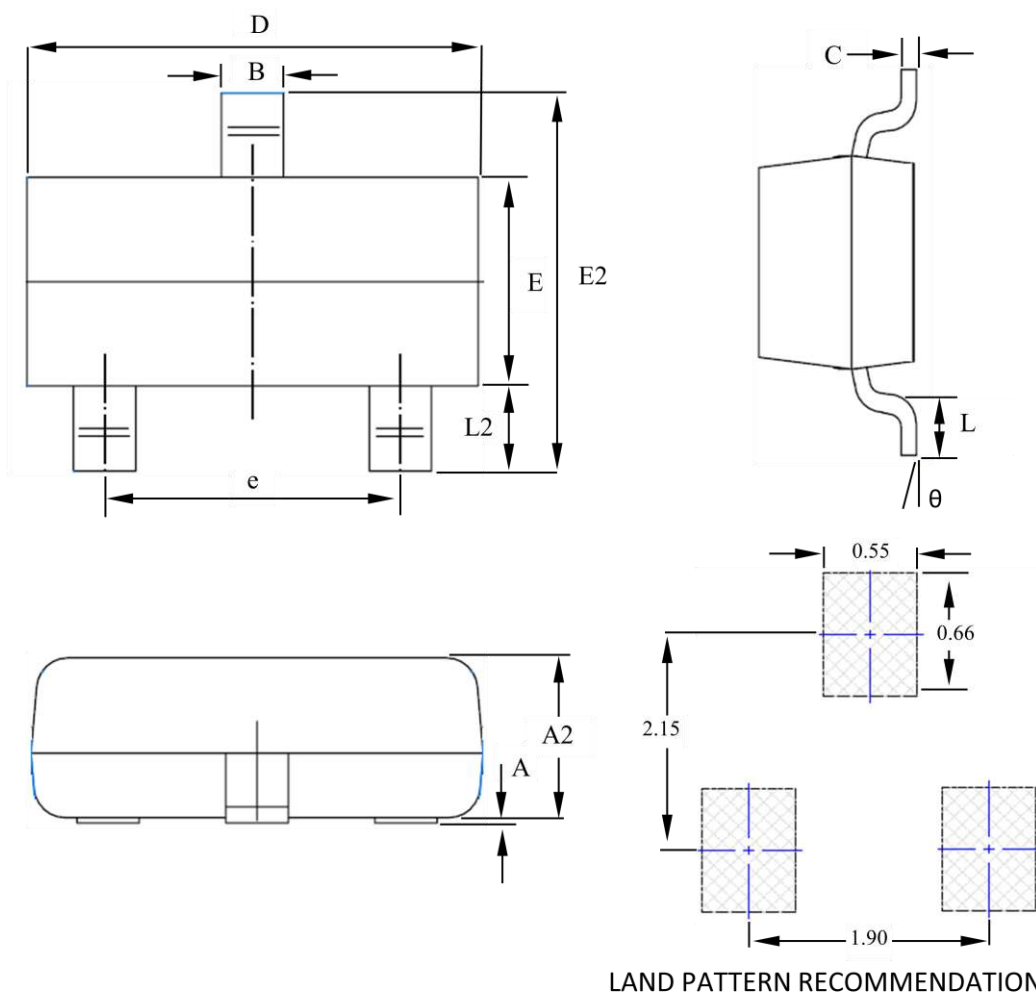


Fig.11 Gate Charge Waveform

SOT-23S Package Outline



SYMBOLS	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.00	--	0.10	0.000	--	0.004
A2	0.90	--	1.10	0.035	--	0.041
B	0.30	--	0.50	0.012	--	0.020
C	0.08	--	0.15	0.003	--	0.006
D	2.80	--	3.00	0.110	--	0.118
E	1.20	--	1.40	0.047	--	0.055
E2	2.25	--	2.55	0.089	--	0.100
L	0.30	--	0.50	0.012	--	0.020
L2	0.50	--	0.60	0.020	--	0.024
θ	0°	--	8°	0°	--	8°
e	1.80	--	2.00	0.071	--	0.079

SOT-23S Carrier & Reel Description

1. Tape and Reel description

Reel Color : Blue or Black

Carrier Tape : Black

Cover Tape : 熱溶性

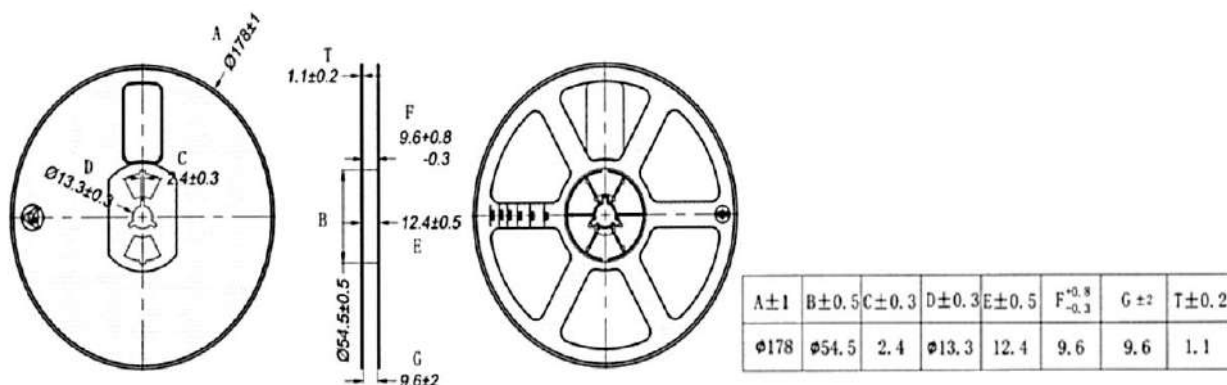
Trailer (後空格) : >300mm

Leader (前空格) : >500mm

Reel 尺寸	卷盤數量	鋁箔袋	內盒數量	外箱數量
7 吋	3,000PCS	3,000PCS	9,000PCS	108,000PCS

備註：外箱依各封測廠現有通用外箱做出貨，故實際外箱數量會有差異。

1.1 Reel Dimensions



1.2. Carrier Tape Dimensions

